20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C (Note 5)
20V	175mΩ @ V_{GS} = 4.5V	1.30A
	240mΩ @ V_{GS} = 2.5V	1.11A
	360mΩ @ V_{GS} = 1.8V	0.91A
	500mΩ @ V_{GS} = 1.5V	0.82A

Features

- Footprint of Just 0.6mm^2 – Thirteen Times Smaller Than SOT23
- 0.4mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

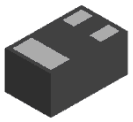
Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)

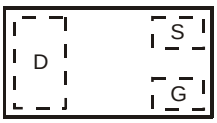
Applications

- Load Switch

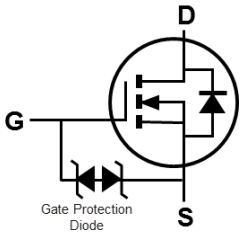
X2-DFN1006-3



Bottom View



Top View



Equivalent Circuit

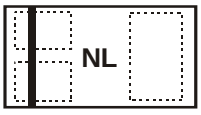
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMN2300UFB4-7B	NL	7	8	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN2300UFB4-7B



Top View
Bar Denotes Gate and Source Side

NL = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +85°C	I_D	1.30 0.96	A
Pulsed Drain Current (Note 6)			I_{DM}	6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	500	mW
Thermal Resistance, Junction to Ambient @T_A = +25°C	$R_{\theta JA}$	250	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	—	0.95	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	175	mΩ	V_{GS} = 4.5V, I_D = 1A
		—	—	240		V_{GS} = 2.5V, I_D = 750mA
		—	—	360		V_{GS} = 1.8V, I_D = 500mA
		—	—	500		V_{GS} = 1.5V, I_D = 200mA
Forward Transfer Admittance	$\|Y_{fs}\|$	40	—	—	mS	V_{DS} = 3V, I_D = 30mA
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 300mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	67.6	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	9.7	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	7.5	—	pF	
Gate Resistance	R_g	—	70	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	1.6	—	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	V_{DS} = 10V, I_D = 1A V_{GS} = 10V, R_G = 6Ω
Turn-On Rise Time	t_R	—	2.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	38	—	ns	
Turn-Off Fall Time	t_F	—	13	—	ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
7. Short duration pulse test used to minimize self-heating effect.

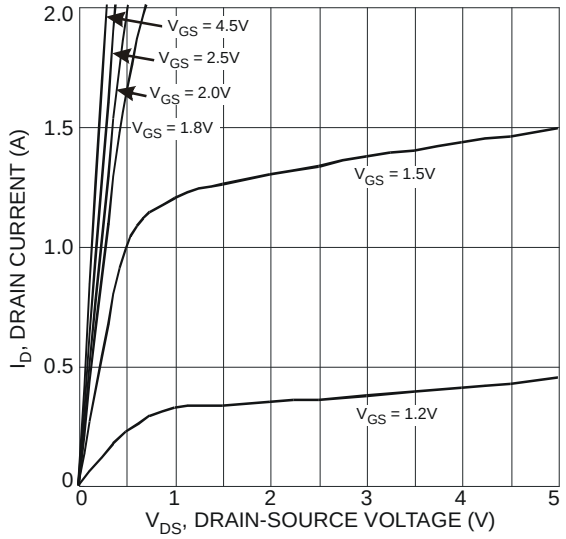


Figure 1 Typical Output Characteristic

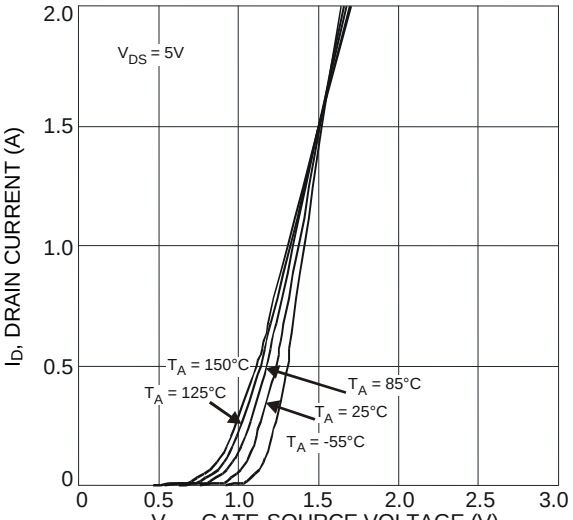


Figure 2 Typical Transfer Characteristic

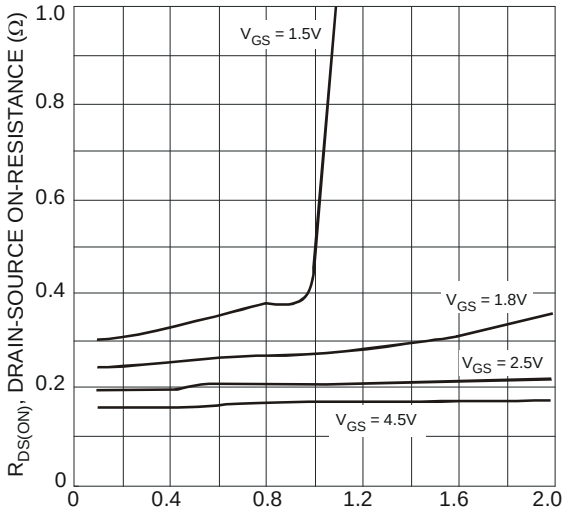


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

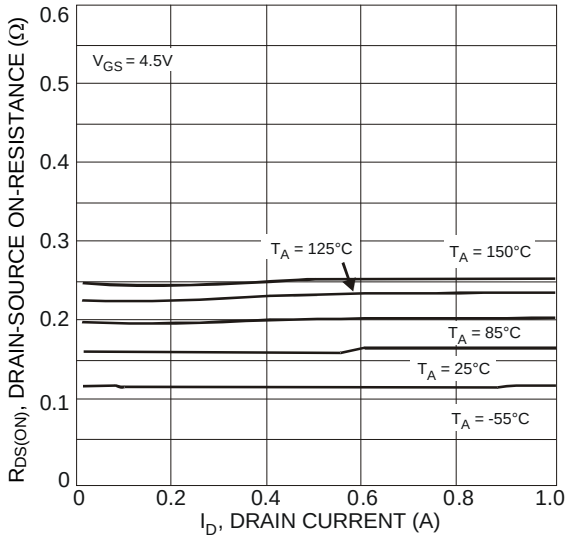


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

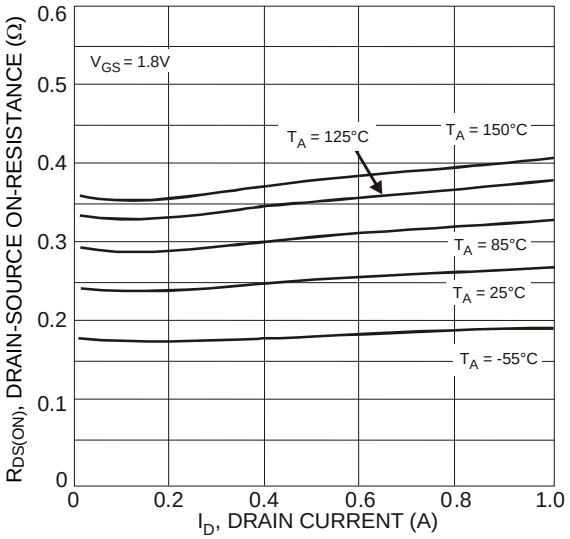


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

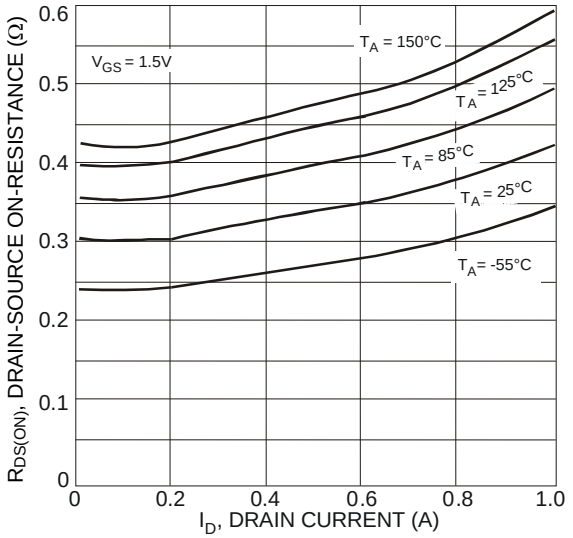


Figure 6 Typical On-Resistance vs. Drain Current and Temperature

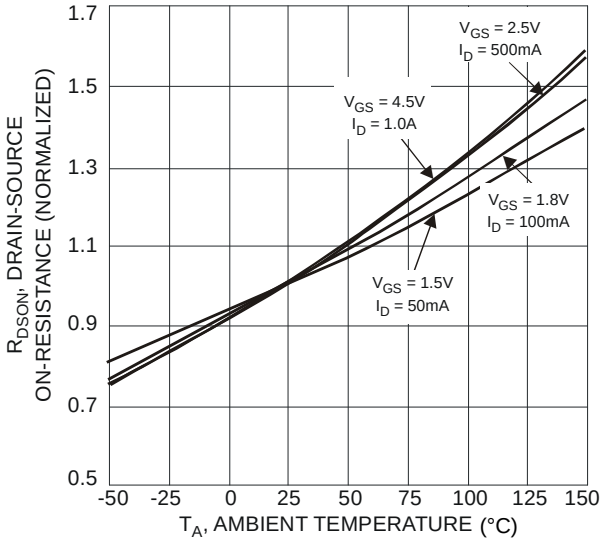


Figure 7 On-Resistance Variation with Temperature

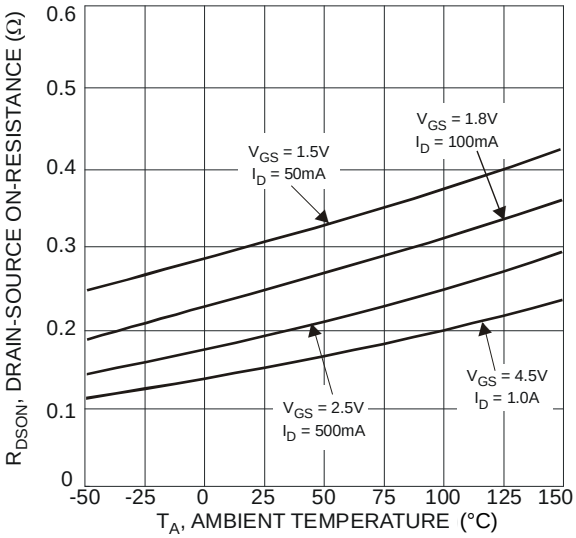


Figure 8 On-Resistance Variation with Temperature

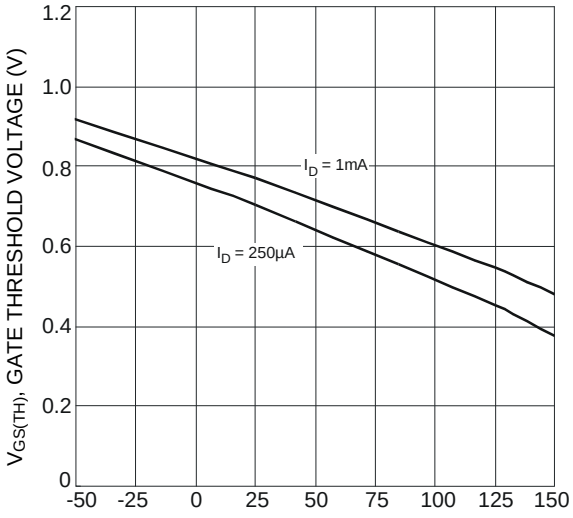


Figure 9 Gate Threshold Variation vs. Ambient Temperature

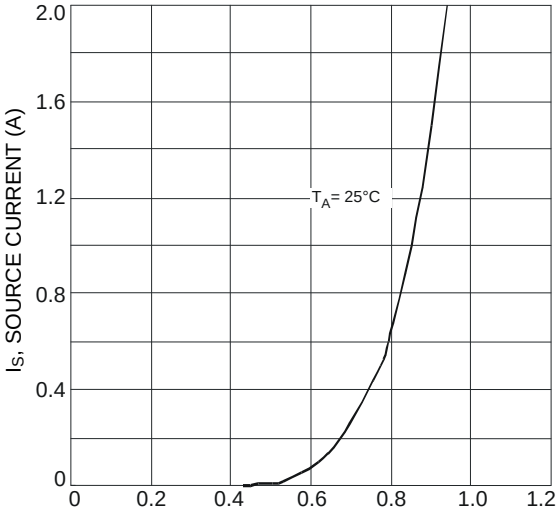


Figure 10 Diode Forward Voltage vs. Current

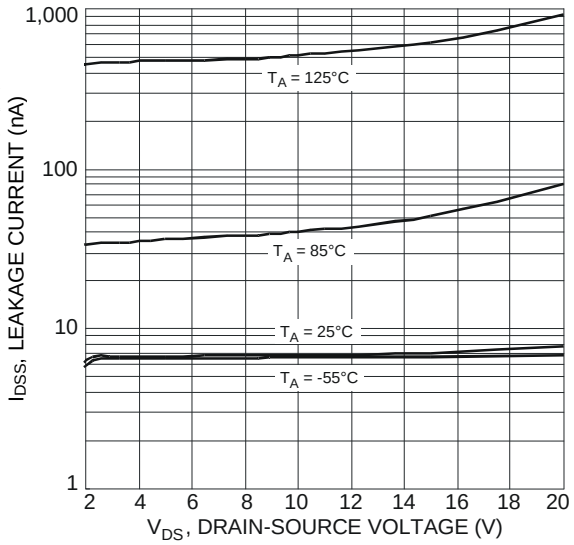


Figure 11 Typical Leakage Current vs. Drain-Source Voltage

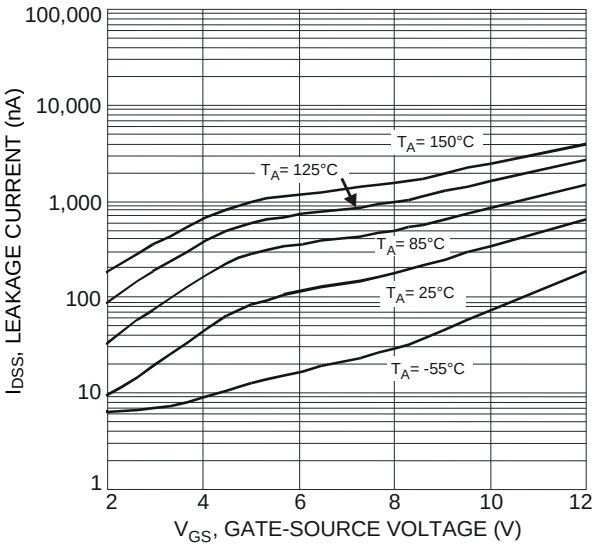


Figure 12 Leakage Current vs. Gate-Source Voltage

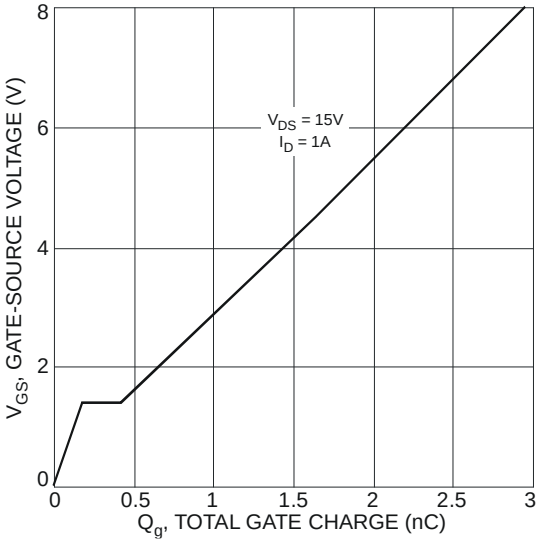


Figure 13 Gate-Charge Characteristics

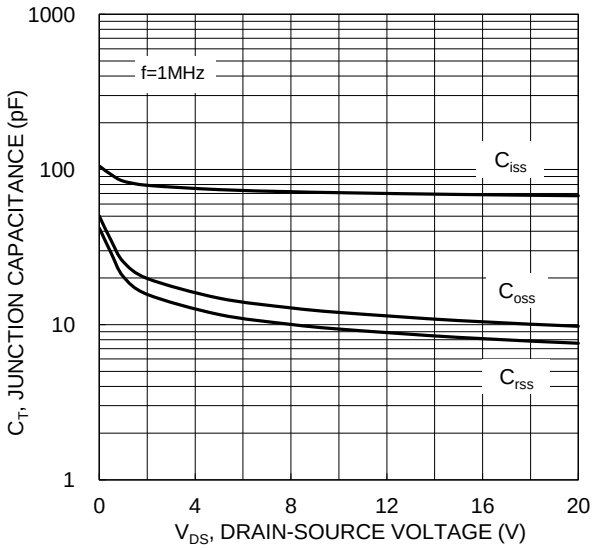


Figure 14 Typical Junction Capacitance

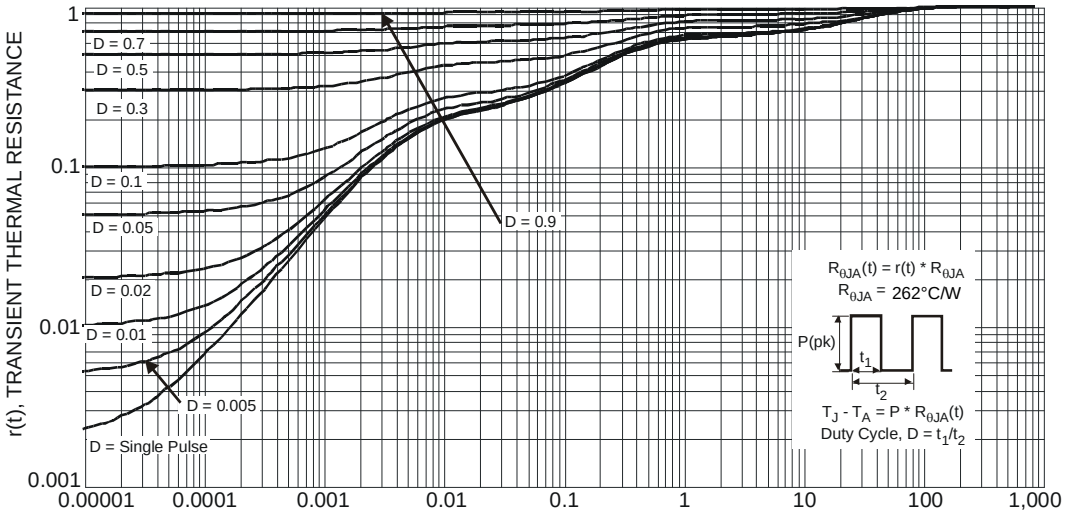
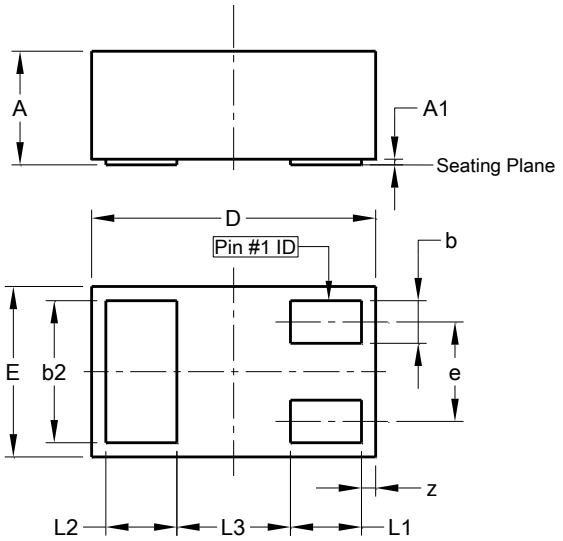


Figure 15 Transient Thermal Response

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

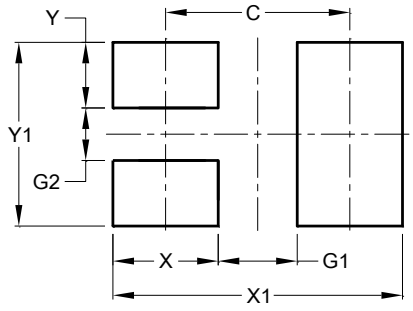


X2-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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